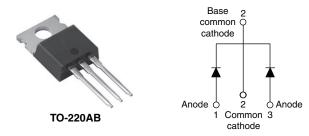


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PRODUCT SUMMARY				
Package	TO-220AB			
I _{F(AV)}	2 x 10 A			
V _R	150 V			
V _F at I _F	0.66 V			
I _{RM} max.	5 mA at 125 °C			
TJ	175 °C			
Diode variation	Common cathode			
E _{AS}	2.45 mJ			

FEATURES

- 175 °C T_J operation
- Low forward voltage drop
- · High frequency operation



COMPLIANT

- High purity, high temperature epoxy encapsulation for enhanced mechanical strength RoHS and moisture resistance
- HALOGEN • Guard ring for enhanced ruggedness and long FREE term reliability
- Compliant to RoHS Directive 2002/95/EC
- Designed and gualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

DESCRIPTION

The center tap Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
I _{F(AV)}	Rectangular waveform	20	A		
V _{RRM}		150	V		
I _{FSM}	t _p = 5 μs sine	1030	А		
V _F	10 A_{pk} , $T_J = 125 \ ^{\circ}C$ (per leg)	0.66	V		
TJ	Range	- 55 to 175	C°		

VOLTAGE RATINGS					
PARAMETER	SYMBOL	VS-20CTQ150PbF	VS-20CTQ150-N3	UNITS	
Maximum DC reverse voltage	V _R	150	150	V	
Maximum working peak reverse voltage	V _{RWM}	150	150	v	

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS					
Maximum average per leg		50 % duty cycle at T_{C} = 154 °C, rectangular waveform		10	А	
See fig. 5 per device	I _{F(AV)}			20		
Maximum peak one cycle		5 μs sine or 3 μs rect. pulse	Following any rated load	1030		
non-repetitive surge current per leg I _{FSM} See fig. 7		10 ms sine or 6 ms rect. pulse	condition and with rated V _{RRM} applied	180	A	
Non-repetitive avalanche energy per leg	E _{AS}	T _J = 25 °C, I _{AS} = 0.7 A, L = 10 mH		2.45	mJ	
Repetitive avalanche current per leg	I _{AR}	Current decaying linearly to zero in 1 μ s Frequency limited by T _J maximum V _A = 1.5 x V _R typical		0.7	А	

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VS-20CTQ150PbF, VS-20CTQ150-N3

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	FIFLIKKAI SPELIEKAIKINS
- 1	ELECTRICAL SPECIFICATIONS

ELECTRICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS			MAX.	UNITS	
Maximum forward voltage drop per leg See fig. 1		10 A	T.I = 25 °C	0.80	0.88	V	
	V (1)	20 A	$1_{\rm J} = 25$ C	0.90	1.0		
	V _{FM} ⁽¹⁾	10 A	T 405 00	0.63	0.66		
		20 A	T _J = 125 °C	0.73	0.77		
Maximum reverse leakage current per leg		T _J = 25 °C			25	μA	
See fig. 2	IRM	T _J = 125 °C	V _R = Rated V _R	2.7	5.0	mA	
Typical junction capacitance per leg	CT	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz) 25 °C		-	280	pF	
Typical series inductance per leg	L _S	Measured lead to lead 5 mm from package body		-	8.0	nH	
Maximum voltage rate of change	dV/dt	Rated V _R		-	10 000	V/µs	

Note

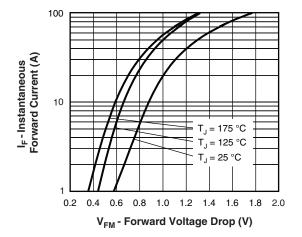
 $^{(1)}\,$ Pulse width < 300 $\mu s,\,duty\,cycle$ < 2 $\,\%$

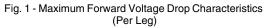
THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		- 55 to 175	°C			
Maximum thermal resistance, junction to case per leg	Б	DC operation	2.0	°C/W			
Maximum thermal resistance, junction to case per package	– R _{thJC}	De operation	1.0				
Typical thermal resistance, case to heatsink	R _{thCS}	R _{thCS} Mounting surface, smooth and greased (Only for TO-220)					
Approvimate weight			2	g			
Approximate weight			0.07	oz.			
Mounting torque	1		6 (5)	kgf ⋅ cm			
Mounting torque maximum			12 (10)	(lbf · in)			
Marking device		Case style TO-220AB	20CT	Q150			

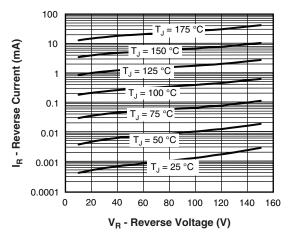


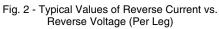
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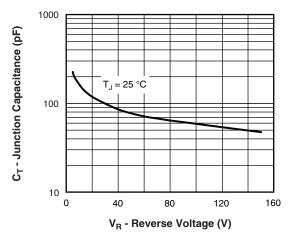
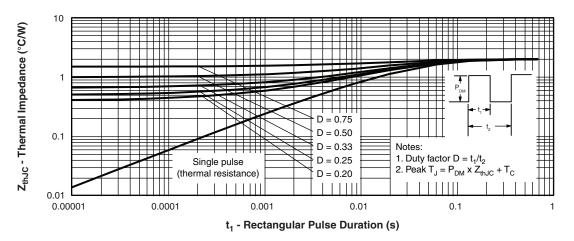
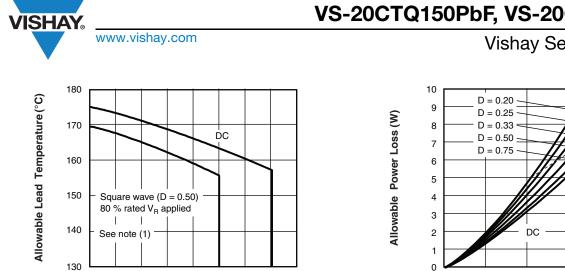


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)





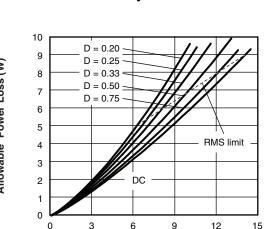
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I_{F(AV)} - Average Forward Current (A)

0 2 4 6 8 10 12 14 16



I_{F(AV)} - Average Forward Current (A)

Fig. 6 - Maximum Average Forward Dissipation vs. Average Forward Current

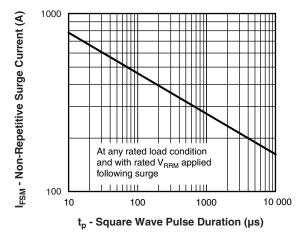


Fig. 7 - Maximum Peak Surge Forward Current vs. Pulse Duration

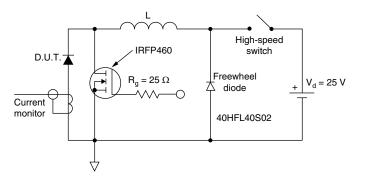


Fig. 8 - Unclamped Inductive Test Circuit

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see fig. 6);

 Pd_{REV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = 80 % rated V_R

Revision: 26-Aug-11

4

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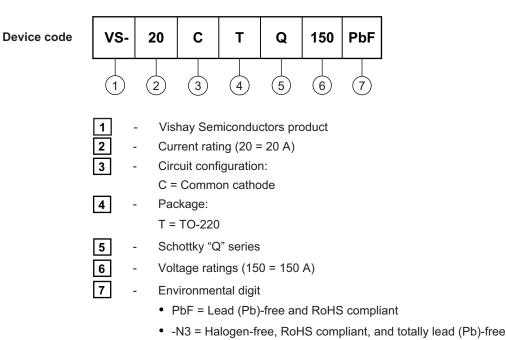
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VS-20CTQ150PbF, VS-20CTQ150-N3



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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)					
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION					
VS-20CTQ150PbF	50	1000	Antistatic plastic tube		
VS-20CTQ150-N3	50	1000	Antistatic plastic tube		

LINKS TO RELATED DOCUMENTS				
Dimensions		www.vishay.com/doc?95222		
	TO-220AB PbF	www.vishay.com/doc?95225		
Part marking information	TO-220AB -N3	www.vishay.com/doc?95028		



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIN	IETERS	INC	INCHES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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